



Integration and Characterization of 4F2 2x-nm Tech 1S1R ReRAM using NbO₂ Selector
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It is reported that 2x nm cross-point ReRAM with 1S1R structure has been successfully developed. Off-current at $1/2 V_{sw}$ of 1S1R is one of key factor for high-density ReRAM. NbO₂ was chosen as a selector material and off-current and forming characteristics were improved by using stack engineering of top and bottom barriers as well as spacer materials. Finally array operation was characterized with the integration of selector and resistor materials.

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